

L Number	Hits	Search Text	DB	Time stamp
1	644	compensat\$5 near mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:14
2	6	(compensat\$5 near mask) and (main near mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:17
3	2	mami near miyasaka	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:19
4	214	(compensat\$5 near mask) and (electron or charged-particle or (charged adj particle))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:20
5	73	((compensat\$5 near mask) and (electron or charged-particle or (charged adj particle))) and stage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:20
6	22	((compensat\$5 near mask) and (electron or charged-particle or (charged adj particle))) and stage) and ((second or two or auxiliary or auxilliary) near mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:33
7	576714	(electron or charged-particle or (charged adj particle))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:34
8	97280	((electron or charged-particle or (charged adj particle))) and stage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:34
9	21650	((electron or charged-particle or (charged adj particle))) and stage) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:34
10	10268	((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:34
11	2035	((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and ((plurality or multiple or two or several) near4 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:35
12	204	((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and (compensat\$5 near4 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:36
13	58	((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and (compensat\$5 near4 mask)) and defect\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:36
14	55	((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and (compensat\$5 near4 mask)) and defect\$5) and (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:37

15	54	(((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and (compensat\$5 near4 mask)) and defect\$5) and (substrate or wafer)) and (resist or photoresist or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:37
16	25	(((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and (compensat\$5 near4 mask)) and defect\$5) and (substrate or wafer)) and (resist or photoresist or film)) and lens and deflect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 06:10
17	4	5888682.URPN.	USPAT	2004/02/23 05:42
20	3	((compensation adj mask) and (charged-particle or (charged adj particle) or electron)) and (stage near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 06:10
19	31	(compensation adj mask) and (charged-particle or (charged adj particle) or electron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 06:11
21	2	("5254438" "5316879").PN.	USPAT	2004/02/23 06:15
18	99	compensation adj mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 06:26

L Number	Hits	Search Text	DB	Time stamp
1	339	auxiliary near mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 08:03
2	94	((auxiliary near mask) and (electron or charged-particle or (charged adj particle)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 08:04
3	42	((auxiliary near mask) and (electron or charged-particle or (charged adj particle))) and stage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 08:04
4	12	((auxiliary near mask) and (electron or charged-particle or (charged adj particle))) and stage) and compensat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:08
5	10268	(electron or charged-particle or (charged adj particle)) and exposure and mask and stage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:09
6	3176	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:09
7	1277	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:10
8	736	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two) near4 (mask or rectile or reticle))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:11
9	854	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:11
10	754	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:12
11	361	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:13

12	354	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:14
13	325	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5) and lens	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:14
14	98	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5) and lens) and defect\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:14
15	6	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5) and lens) and defect\$5) and (non-defect\$5 or nondefect\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:22
16	49	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5) and lens) and defect\$5) and compensat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:55
17	108	compensation adj (mask or reticle or rectile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:56
18	34	(compensation adj (mask or reticle or rectile)) and (electron or charged-particle or (charged adj particle))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:00
19	20	((compensation adj (mask or reticle or rectile)) and (electron or charged-particle or (charged adj particle))) and exposure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:57
20	1030	(electron or charged-particle or (charged adj particle)) and ((wafer or substrate) near stage) and ((reticle or rectile or mask) near stage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:02

21	245	((electron or charged-particle or (charged adj particle)) and ((wafer or substrate) near stage) and ((reticle or rectile or mask) near stage)) and ((two or second) near (mask or reticle or rectile))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:17
22	1587	((two or second) near (mask or reticle or rectile)) and ((correct\$4 or reference) near2 (mask or reticle or rectile))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:19
23	11	(((two or second) near (mask or reticle or rectile)) and ((correct\$4 or reference) near2 (mask or reticle or rectile))) and (non-defective)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:21
24	2512	((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:36
25	396	((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle)) and ((wafer or sample or substrate)near stage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:37
26	245	((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle)) and ((wafer or sample or substrate)near stage)) and ((mask or rectile or reticle) near stage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:38
27	220	((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle)) and ((wafer or sample or substrate)near stage)) and ((mask or rectile or reticle) near stage)) and ((electron or charged-particle or (charged adj particle)) near beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:39
28	193	((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle)) and ((wafer or sample or substrate)near stage)) and ((mask or rectile or reticle) near stage)) and ((electron or charged-particle or (charged adj particle)) near beam)) and ((resist or photoresist or film) with (substrate or wafer or sample))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:40
29	185	((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle)) and ((wafer or sample or substrate)near stage)) and ((mask or rectile or reticle) near stage)) and ((electron or charged-particle or (charged adj particle)) near beam)) and ((resist or photoresist or film) with (substrate or wafer or sample))) and (lens or (electron near optic\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:40

30	178	(((((((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate)near stage)) and ((mask or rectile or reticle) near stage)) and ((electron or charged-particle or (charged adj particle)) near beam)) and ((resist or photoresist or film) with (substrate or wafer or sample))) and (lens or (electron near optic\$3))) and control\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:41
31	58	(((((((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate)near stage)) and ((mask or rectile or reticle) near stage)) and ((electron or charged-particle or (charged adj particle)) near beam)) and ((resist or photoresist or film) with (substrate or wafer or sample))) and (lens or (electron near optic\$3))) and control\$4) and defect\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:41